SILICON (Si) POWER MOSFET ▲ CEB16N10



CEB16N10

100V ▲ 100mΩ ▲ 15.2A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO263 (D2PAK) package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability





RoHS

REACH

MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	100V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _c = 25°C	I _D	15.2A
Pulsed Drain Current Note 1	I _{DM}	60A
Maximum Power Dissipation at T _c = 25°C	PD	60W
Power Dissipation Derating above 25°C	ΔP _D	0.48W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

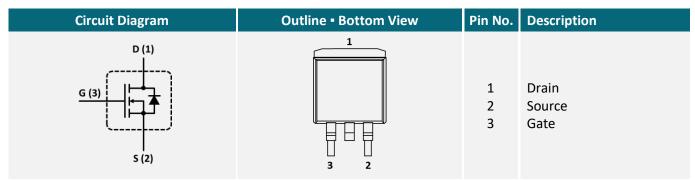
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	2.5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	50°C/W

APPLICATIONS

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+ 4 -	50			

PIN DESCRIPTION



CEB16N10 ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 1

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ELECTRICAL CHARACTERISTICS A T_c = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV _{DSS}	100			V
Zero Gate Voltage Drain Current	V_{DS} = 100V, V_{GS} = 0V	I _{DSS}			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V$, $V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	2		4	V
Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 7A	R _{DS(ON)}		100	120	mΩ
Forward Transconductance	V _{DS} = 10V, I _D = 7A	g _{FS}		5		S
Dynamic Characteristics Note 3						
Input Capacitance	V_{DD} = 25V, V_{GS} = 0V, f = 1MHz	CISS		540		рF
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	Coss		105		рF
Reverse Transfer Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{RSS}		25		pF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 15A, $R_{G(ext)}$ = 25 Ω	t _{D(ON)}		14	40	ns
Turn-On Rise Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 15A, $R_{G(ext)}$ = 25 Ω	t _R		3	7	ns
Turn-Off Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 15A, $R_{G(ext)}$ = 25 Ω	t _{D(OFF)}		32	70	ns
Turn-Off Fall Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 15A, $R_{G(ext)}$ = 25 Ω	t _F		7	15	ns
Total Gate Charge	V_{DD} = 80V, V_{GS} = 10V, I_D = 15A	Q _G		11	16	nC
Gate Source Charge	V_{DD} = 80V, V_{GS} = 10V, I_D = 15A	Q _{GS}		2.8		nC
Gate Drain Charge	V_{DD} = 80V, V_{GS} = 10V, I_{D} = 15A	Q_{GD}		3.7		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		I _S			15.2	А
Drain-Source Diode Forward Voltage Note 2	V _{GS} = 0V, I _S = 15.2A	V_{SD}			1.5	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

3: Guaranteed by design, not subject to production testing.

4: L = 0.7mH, I_{AS} = 15.2A, V_{DD} = 25V, R_G = 25 Ω , Starting T_J = 25°C

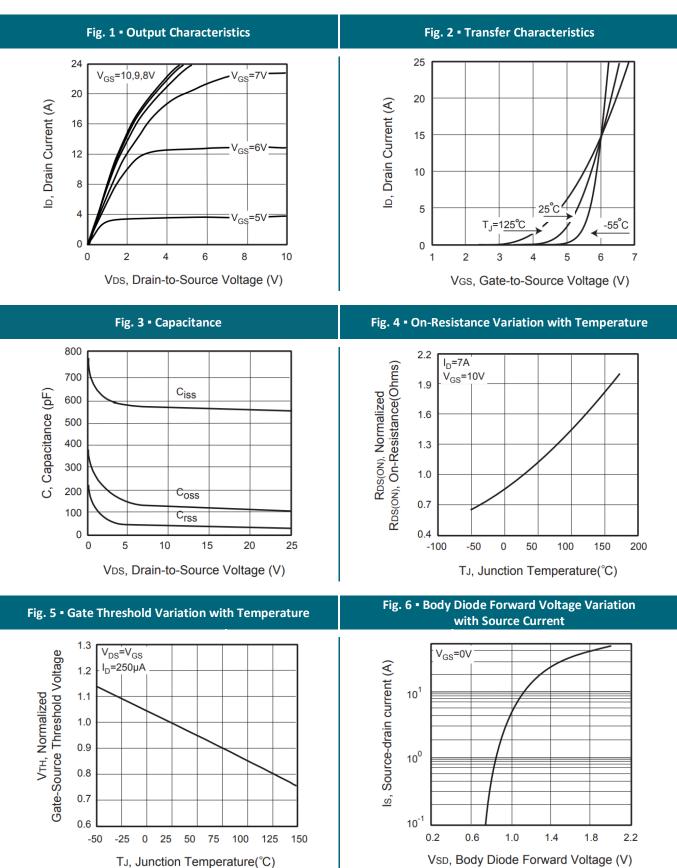


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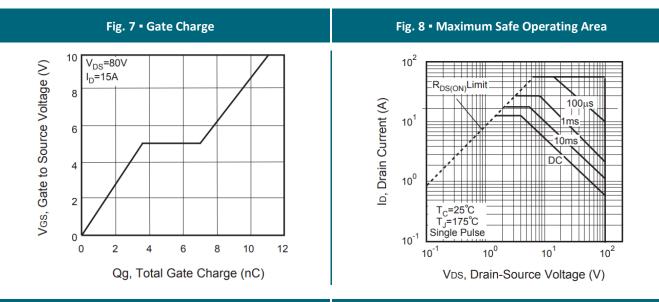
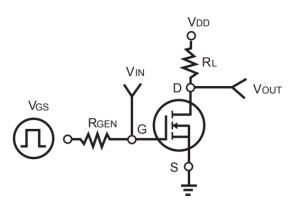


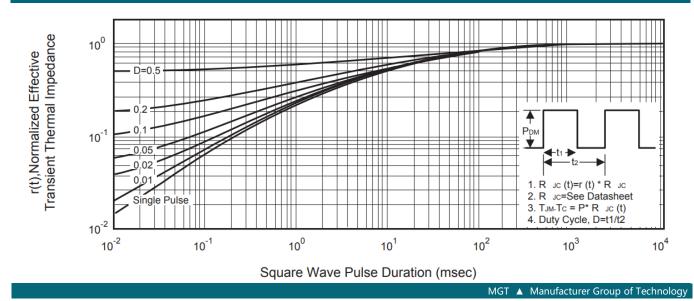
Fig. 9 - Switching Test Circuit



← ton → - toff – td(off) tr td(on) tf 90% 90% VOUT 10% **INVERTED** 10% 90% 50% 50% Vin 10% PULSE WIDTH

Fig. 10 - Switching Waveforms

Fig. 11 • Switching Test Circuit

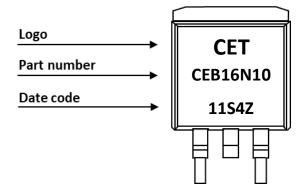


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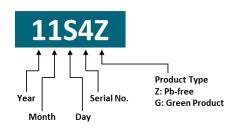






DATE CODE

Example: 11S4Z



Coding list for "Day"

1 01	2 02	3 03	4 04	5 05	6 06	7 07	8 08	9 09	A 10
В	С	D	E	F	G	н	I	J	К
11 L	12 M	13 N	14 O	15 P	16 Q	17 R	18 S	19 T	20 U
21	22	23	24	25	26	27	28	29	30
V									
31									

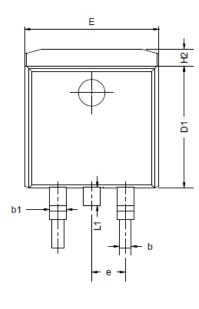
Coding list for "Month"

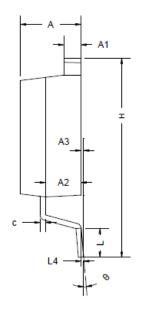
1 an 1	2 Feb	3 Mar	4 Apr	5 May	6 Jun					
7 Iul ,	8 Aug	9 Sep	A Oct	B Nov	C Dec					
Coding list for "Year"										
0	1	2	3	3 4	L.					
2020	202:	1 202	22 20	23 202	24					
5	6	7	8	3 9)					
2025	2026	5 202	27 20	28 20	29					

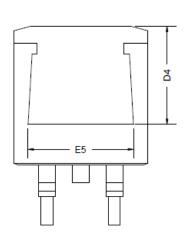
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PACKAGE OUTLINE







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.37	4.57	4.77	E	9.86	10.16	10.36
A1	1.22	1.27	1.42	E5	7.06	-	-
A2	2.49	2.69	2.89	е		2.54 BSC	
A3	0.00	0.13	0.25	Н	14.70	15.10	15.50
b	0.70	0.81	0.96	H2	1.07	1.27	1.47
b1	1.17	1.27	1.47	L	2.00	2.30	2.60
с	0.30	0.38	0.53	L1	1.40	1.55	1.70
D1	8.50	8.70	8.90	L4		0.25 BSC	
D4	6.60	-	-	θ	0°	5°	9°

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEB16N10	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs

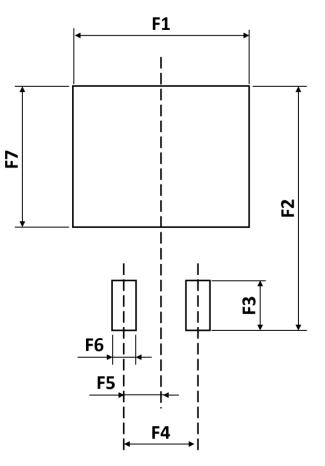
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RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-	F5	-	2.54	-
F2	-	16.90	-	F6	-	1.60	-
F3	-	2.54	-	F7	-	9.75	-
F4	-	5.08	-				

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

CEB16N10 ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 7

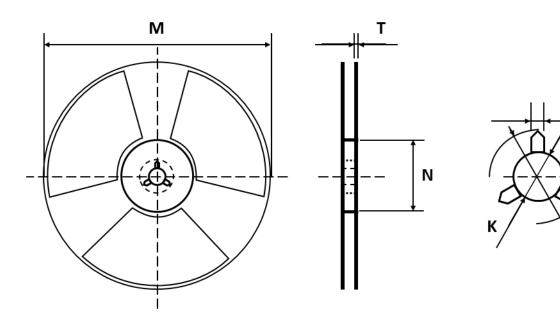


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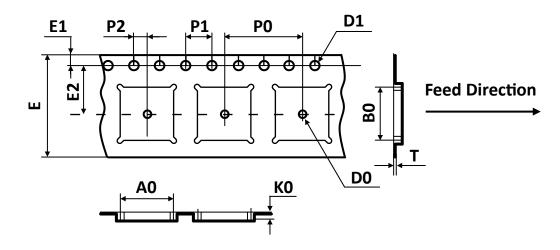


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ² PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

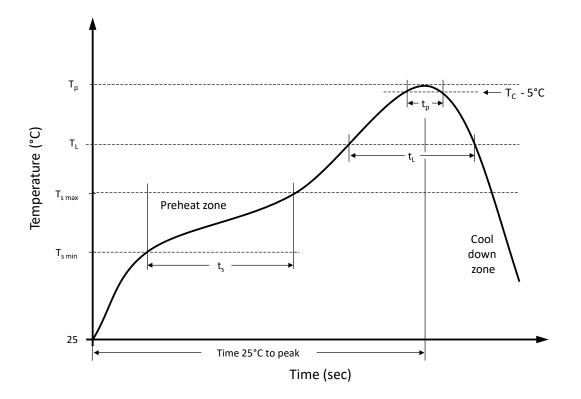


CEB16N10 ARev.001 ADate: 30/09/2022 APage: 8





RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	T_{smax}	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time t_L maintained above T_L	tL	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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